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thin solid films

Contents

Letters

Hydrogen and deuterium migration in annealed plasma-deposited silicon nitride films 1
C. Savall and J. C. Bruyère (Grenoble, France)

Characteristics of Pt thin films on the conducting ceramics TiO and Ebonex (Ti_4O_7) as electrode materials 5
S.-Y. Park, S.-I. Mho, E. O. Chi, Y. U. Kwon (Suwon, South Korea) and H. L. Park (Seoul, South Korea)

^{13}C nuclear magnetic resonance signals of Ge/C films deposited from tetraethylgermanium in an r.f. glow discharge..... 10
M. Gazicki, M. J. Portzebowski, J. Tyczkowski (Łódź, Poland) and J. Schalko (Vienna, Austria)

Synthesis and Characterization

High power deposition and analytics of amorphous silicon carbide films 14
R. Heyner and G. Marx (Chemnitz, Germany)

Growth of boron nitride thin films by metal–organic chemical vapour deposition 21
A. Ratna Phani, S. Roy and V. J. Rao (Hyderabad, India)

Thickness variation effects on X-ray scattering of multilayers 26
A. Boufelfel (Guelma, Algeria) and C. M. Falco (Tuscon, AZ, USA)

Thermal stability of pulsed laser deposited diamond-like carbon films 34
C. W. Ong, X.-A. Zhao, J. T. Cheung, S. K. Lam, Y. Liu, C. L. Choy and P. W. Chan (Kowloon, Hong Kong)

Laser reactive ablation deposition of titanium carbide films 40
G. Leggieri, A. Luches, M. Martino, A. Perrone (Lecce, Italy), G. Majni, P. Mengucci (Ancona, Italy) and I. N. Mihailescu (Bucharest, Romania)

Sputter ion plating of tungsten on CVD grown diamonds for laser thermal diffusivity measurement 46
N. A. G. Ahmed (Salford, UK) and S. D. Preston (Warrington, UK)

Structure of $TiN_x (0 < x < 1.1)$ films prepared by ion beam-assisted deposition 51
H. Jiang, K. Tao and H. Li (Beijing, People's Republic of China)

Structures of tantalum pentoxide thin films formed by reactive sputtering of Ta metal 56
P.-H. Chang (Sinchu, Taiwan) and H.-Y. Liu (Dallas, TX, USA)

Preparation of SiC films by solid state source evaporation 64
A. Fissel, B. Schröter, J. Kräußlich and W. Richter (Jena, Germany)

Characterization of trimethylaluminum-N_2O–He glow discharge in plasma-enhanced chemical vapor deposition of aluminum oxide films 67
Y.-C. Kim, J. S. Chun (Taejon, South Korea) and W.-J. Lee (Kyunki-Do, South Korea)

Nanotribological characterization of hydrogenated carbon films by scanning probe microscopy 75
Z. Jiang, C.-J. Lu, D. B. Bogy, C. S. Bhatia and T. Miyamoto (Berkeley, CA, USA)

Low temperature synthesis of $Pb_{1-x}La_x(Zr_{1-y}Ti_y)_{1-x/4}O_3$ films by pulsed laser deposition 82
M. H. Yeh, K. S. Liu and I. N. Lin (Hsinchu, Taiwan)

Growth and characterization of polycrystalline InSe thin films 86
M. Parlak, Ç. Erçelebi, I. Günal (Ankara, Turkey), Z. Salaeva (Baku, Azerbaijan) and K. Allakhverdiev (Ankara, Turkey)

Ion-beam sputtering of $(Ta_2O_5)_x$–$(SiO_2)_{1-x}$ composite thin films 91
M. Cevro (Salford, UK)

Modeling of the formation of RuO_2 thin film from $Ru(C_5H_5)_2$ by metal–organic chemical vapor decomposition..... 104
S. Y. Mar, Y. S. Huang (Taipei, Taiwan) and K. K. Tiong (Keelung, Taiwan)

Elsevier Science S.A.

X-ray photoelectron spectroscopy characterization of amorphous molybdenum oxysulfide thin films 110
L. Benoist, D. Gonbeau, G. Pfister-Guillouzo (Pau, France), E. Schmidt, G. Meunier and A. Levasseur (Talence Cedex, France)

Whisker growth on sputtered AlSn (20 wt.% Sn) films..... 115
A. Bergauer, H. Bangert, Ch. Eisenmenger-Sittner (Vienna, Austria) and P. B. Barna (Budapest, Hungary)

Microstructural modifications in diamond-like carbon thin films caused by high energy ion irradiation..... 123
H. C. Barshilia, S. Sah, B. R. Mehta, V. D. Vankar, D. K. Avasthi, Jaipal and G. K. Mehta (Delhi, India)

In situ stress measurements of Co/Pd multilayer films using an optical non-contact displacement detector..... 128
Y.-S. Kim and S.-C. Shin (Taejon, South Korea)

Surfaces, Interfaces and Colloidal Behaviour

Interface properties of a-Si:H/a-SiC_x:H superlattice 132
G. Chen, Y. Guo, J. Yao, Z. Song and F. Zhang (Lanzhou, People's Republic of China)

Surface segregation of boron atoms in Si and strained $Si_{1-x}Ge_x$ layers during MBE growth: experiment and simulation. 137
D. Krüger and H. J. Osten (Frankfurt, Germany)

XPS and AES characterization of SiN_x:H layers deposited by PECVD on Parylene C. Effects of thermal treatments on Parylene C surfaces and Parylene C/SiN_x:H interlayers 143
E. Bêche (Belfort, France), R. Berjoan (Font Romeu, France), J. Viard (Montpellier, France), B. Cros (Belfort, France) and J. Durand (Montpellier, France)

Metallurgical and Protective Hard Layers

Influence of reactant gas composition on selected properties of N-doped hydrogenated amorphous carbon films 151
P. Wood, T. Wydevan (Sunnyvale, CA, USA) and O. Tsuji (Kyoto, Japan)

A quantitative model for the evolution from random orientation to a unique texture in PVD thin film growth 159
G. Knuyt, C. Quaeyhaegens, J. D'Haen and L. M. Stals (Diepenbeek, Belgium)

Experimental study of the growth evolution from random towards a (111) preferential orientation of PVD TiN coatings 170
C. Quaeyhaegens, G. Knuyt, J. D. D'Haen and L. M. Stals (Diepenbeek, Belgium)

Zirconocene-modified polysiloxane-2-pyridine coatings 174
T. Sugama, N. Carciello (Upton, NY, USA) and S. L. Rast (Ocala, FL, USA)

Study and improvement of the adhesion of chromium thin films deposited by magnetron sputtering..... 185
V. Guilbaud-Massereau, A. Celerier and J. Machet (Limoges, France)

Improving the passivating efficiency of conversion films on stainless steel by thermal treatment 194
M. J. Carmezim (Setúbal, Portugal), F. G. Carvalho (Sacavém, Portugal) and M. O. Figueiredo (Mjonte de Caparica, Portugal)

Mechanics and Nanomechanics of Thin Layers

Finite element analysis of the critical ratio of coating thickness to indentation depth for coating property measurements by nanoindentation 198
Y. Sun, T. Bell and S. Zheng (Birminghan, UK)

Adhesion and X-ray elastic constant evaluation of CrN coating..... 205
F. Attar (Linköping, Sweden) and T. Johannesson (Lund, Sweden)

Electronics, Optics and Opto-electronics

Optical properties of thin films up to second order in the thickness 213
M. T. Haarmans and D. Bedeaux (Leiden, Netherlands)

Attenuation, scattering, and absorption properties of light emitting planar waveguides..... 224
L. Schrottke (Berlin, Germany)

Rapid thermal processed thin films of reactively sputtered Ta_2O_5 230
A. Pignolet, G. Mohan Rao and S. B. Krupanidhi (University Park, PA, USA)

Resistance behaviour and interdiffusion of layered CuNi–NiCr films 236
W. Brückner, J. Schumann, S. Baunack, W. Pitschke (Dresden, Germany) and Th. Knuth (Teltow, Germany)

Surface-plasmon-enhanced diffraction orders in polymer gratings..... 247
B. Fischer, B. Rothenhäusler and W. Knoll (Mainz, Germany)

Oxidation behaviour of Cu–Ni(Mn) (constantan) films 252
W. Brückner, S. Baunack, G. Reiss, G. Leitner (Dresden, Germany) and Th. Knuth (Teltow, Germany)

Indium tin oxide on InP by pulsed laser deposition 260
Q. X. Jia (Los Alamos, NM, USA), J. P. Zheng (Fort Monmouth, NJ, USA), H. S. Kwok and W. A. Anderson (Buffalo, NY, USA)

Epitaxial and thermal strains in oxidic thin films on Si(001) 264
Th. Matthée, J. Wecker (Erlangen, Germany), A. Bardal (Trondheim, Norway) and K. Samwer (Augsburg, Germany)

Sol–gel-derived tin oxide thin films 268
S.-S. Park and J. D. Mackenzie (Los Angeles, CA, USA)

Effects of oxygen partial pressure on the microstructure and electrical properties of indium tin oxide film prepared by d.c. magnetron sputtering 274
C. G. Choi, K. No, W.-J. Lee, H.-G. Kim, S. O. Jung, W. J. Lee (Taejon, South Korea), W. S. Kim, S. J. Kim and C. Yoon (Kyong Sang Buk-Do, South Korea)

Transient behaviour of thin film transistors based on nickel phthalocyanine 279
G. Guillaud, R. Ben Chaabane, C. Jouve and M. Gamoudi (Villeurbanne, France)

Radiation damage in indium tin oxide (ITO) layers 283
D. V. Morgan, A. Salehi, Y. H. Aliyu, R. W. Bunce (Cardiff, UK) and D. Diskett (Swindon, UK)

Fast-ion-induced fluorescence from J aggregate of cyanine dye in Langmuir–Blodgett films 286
K. Asai, S. Seki, T. Sato, K. Ishigure (Tokyo, Japan) and H. Shibata (Ibaraki, Japan)

Effects of nitrogen trifluoride on the properties of plasma-enhanced chemical-vapor-deposited semi-insulating polysilicon films 292
R. M. Ranade, S. S. Ang and W. D. Brown (Fayetteville, AR, USA)

Superconductivity

The effect of a MgO seed layer on the biepitaxial growth of $Y_1Ba_2Cu_3O_{7-x}$ overlayers in various multilayered thin films 299
S. Lee, S. Oh, D. Goo and D. Youm (Taejon, South Korea)

Langmuir–Blodgett, Biological and Related Films

Interlayer energy transfer between chromophoric carbazole and oxacyanine in Langmuir–Blodgett films: site selectivity of trapping 305
N. Ohta, S. Okazaki, S. Yoshinari and I. Yamazaki (Sapporo, Japan)

Thin Film Devices, Sensors and Actuators

Composition monitoring method in $CuInSe_3$ thin film preparation 313
M. Nishitani, T. Negami and T. Wada (Kyoto, Japan)

Charge transport in thin films of molecular semiconductors as investigated by measurements of thermoelectric power and electrical conductivity 317
J.-P. Meyer, D. Schlettwein, D. Wöhrle and N. I. Jaeger (Bremen, Germany)

Condensed Matter Film Behaviour

Preparation and characterisation of poly[octyl 1,2-(2′,2″-dithienylacrylate)] thin films 325
Z.-S. Jin, C. Conn, J. Unsworth, R. N. Ediriweera, J. Kurusingal and S. M. Pillai (Sydney, Australia)

Microstructure of gold grown by ion-induced deposition 333
J. S. Ro, C. V. Thompson and J. Melngailis (Cambridge, MA, USA)

Concentration-dependent redistribution of arsenic in silicon during thermal oxidation 336
S. S. Choi, M. J. Park and W. K. Chu (Chung Nam, South Korea)

Formation of anodic alumina films in tungstate/ethylene glycol electrolyte 341
J. R. Morlidge (Manchester, UK), K. Shimizu (Yokohama, Japan), P. Skeldon, G. E. Thompson and G. C. Wood (Manchester, UK)

Activation energy of hopping conductivity in low-doped and low-compensated semiconductor films 347
S. L. Haroutunian, V. A. Haroutunian, H. A. Jivanian and G. H. Demirjian (Yerevan, Armenia)

Announcements 351

Author Index 353

Subject Index 355